will rise with increased pressure because of the rise in p_n. In the case of low ohmic germanium τ_e increases with an increase in the injection level [8].

In conclusion it should be noted that at low reverse voltages and comparatively low pressures (up to $3 \cdot 10^9$ dyne/cm^2) there is a correlation between the change in the diode reverse current with low bias and the change in τ_e, which is expressed by the formula

$$j_s = \frac{q p_n \sqrt{D_p}}{\sqrt{\tau_p}} .$$ (5)

The change in D_p with increasing pressure can be ignored since it is very small [3].

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